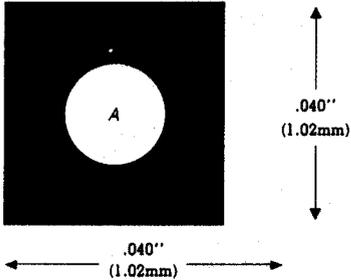


**CHIP NUMBER**

**500**



**PN EPITAXIAL PLANAR POWER DIODE**

**CONTACT METALLIZATION**

Anode: > 30,000 Å Aluminum

Cathode: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

**MOLY PEDESTAL**

Size: .140" Diameter (3.56mm)

Thickness: .010" (0.25mm)

**ASSEMBLY RECOMMENDATIONS**

It is advisable that:

- a) the chip be eutectically mounted with gold silicon preform 98/2%.
- b) 8 mil (0.203mm) aluminum wire be ultrasonically attached to the anode contact.

Anode: .020" (0.51mm) dia.

**TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C**

The following typical electrical characteristics apply for a completely finished component employing the chip number 500 in a DO-4 or equivalent case:

Minimum $V_R$ @ 10 $\mu A$	$I_R$ @ 80% $V_R$	$V_F$ @	$I_F$	$I_F$ Surge	Maximum $t_{tr}$ @ $I_F = I_R = 1.0A$ $I_{REC} = 0.25A$
> 50V	< 5 $\mu A$	1.2V	1.5A	> 100A	200 ns
> 100V	< 5 $\mu A$	1.2V	1.5A	> 100A	200 ns
> 200V	< 5 $\mu A$	1.2V	1.5A	> 100A	200 ns
> 300V	< 5 $\mu A$	1.2V	1.5A	> 100A	200 ns
> 400V	< 5 $\mu A$	1.2V	1.5A	> 100A	450 ns
> 500V	< 5 $\mu A$	1.2V	1.5A	> 100A	450 ns

TYPICAL DEVICE TYPES: 1N5614, 1N5615, 1N5616

$I_F$  surge  $\geq 60A$ .